NSN 5962-01-138-6199

Memory Microcircuit - Page 1 of 1

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Maximum Power Dissipation Rating:

500.0 milliwatts

Operating Tempurature Range:

-0.0/+75.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

W/enable and hermetically sealed and 3-state output and monolithic

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

10 input

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Time Rating Per Chacteristic:

60.00 nanoseconds propagation delay time, low to high level output and 60.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Rom

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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